

## 2009 — FUJIWARA Yasufumi

### Scientific Papers/Commentary Articles

1. A. Nishikawa, T. Kawasaki, N. Furukawa, Y. Terai and Y. Fujiwara, Electroluminescence properties of Eu-doped GaN-based red light-emitting diode by OMVPE, *physica status solidi A*, in press, 印刷中
2. T. Kawasaki, A. Nishikawa, N. Furukawa, Y. Terai and Y. Fujiwara, Effect of Growth Temperature on Eu-Doped GaN Layers Grown by Organometallic Vapor Phase Epitaxy, *physica status solidi C*, 印刷中
3. Y. Terai, K. Yamaoka, K. Yoshida, T. Tsuji and Y. Fujiwara, Photoluminescence properties of Eu-doped ZnO films grown by sputtering-assisted metalorganic chemical vapor deposition, *Physica E*, 印刷中
4. Y. Terai, T. Tsuji, K. Noda and Y. Fujiwara, Photoluminescence properties of Er-doped  $\beta$ -FeSi<sub>2</sub> grown by ion implantation, *Physica E*, 印刷中
5. Y. Konaka, K. Ono, Y. Terai and Y. Fujiwara, Coexistence properties of phase separation and CuPt-ordering in InGaAsP grown on GaAs substrates by organometallic vapor phase epitaxy, *Journal of Crystal Growth*, 印刷中
6. H. Kasai, A. Nishikawa, T. Kawasaki, N. Furukawa, Y. Terai, and Y. Fujiwara, Improved Eu luminescence properties in Eu-doped GaN grown on GaN substrates by organometallic vapour phase epitaxy, *Japanese Journal of Applied Physics*, Vol. 49, 048001/1-2, 2010
7. A. Nishikawa, H. Kasai, T. Kawasaki, Y. Terai, Y. Fujiwara, Optical properties of Eu-implanted GaN and related-alloy semiconductors, *Journal of Physics: Conference Series*, Vol. 191, 012028/1-4, 2009
8. Y. Fujiwara, K. Fujii, A. Fujita, Y. Ota, Y. Ito, T. Kawasaki, K. Noguchi, T. Tsuji, A. Nishikawa, and Y. Terai, Luminescence properties in Er,O-codoped GaAs light-emitting devices with double excitation mechanism, *Materials Research Society Symposium Proceedings, Rare-Earth Doping of Advanced Materials for Photonic Applications*, Vol. 1111, 143-148, 2009
9. Y. Terai, K. Yamaoka, T. Yamaguchi and Y. Fujiwara, Structural and luminescent properties of Er-doped ZnO films grown by metalorganic chemical vapor deposition, *Journal of Vacuum Science and Technology*, Vol. 27, 2248-2251, 2009
10. A. Nishikawa, T. Kawasaki, N. Furukawa, Y. Terai, Y. Fujiwara, Room-temperature red emission from a p-type/europium-doped/n-type gallium nitride light-emitting diode under current injection, *Applied Physics Express*, Vol. 2, 071004/1-3, 2009
11. Y. Terai, S. Hashimoto, K. Noda and Y. Fujiwara, Epitaxial growth of Al-doped  $\beta$ -FeSi<sub>2</sub> on Si(111) substrate by reactive deposition epitaxy, *Physica Status Solidi (c)*, Vol. 6, 1488-1491,

2009

12. K. Noda, Y. Terai, S. Hashimoto, K. Yoneda, and Y. Fujiwara, Modifications of direct transition energies in b-FeSi<sub>2</sub> epitaxial films grown by molecular beam epitaxy, *Applied Physics Letters*, Vol. 94, 241907/1-3, 2009
13. Y. Terai, T. Tokuno, H. Ichida, Y. Kanematsu and Y. Fujiwara, Electroluminescence properties of GaInP/GaAs:Er,O/GaInP double heterostructure light-emitting diodes at low temperature, *Optical Materials*, Vol. 31, 1323-1326, 2009
14. Y. Ota, K. Fujii, Y. Ito, T. Kawasaki, K. Noguchi, T. Tsuji, Y. Terai, and Y. Fujiwara, Optical properties of GaInP/GaAs:Er,O/GaInP laser diodes grown on p-type GaAs substrates by organometallic vapor phase epitaxy, *IOP Conference Series: Materials Science and Engineering*, Vol. 1, 012022/1-4, 2009
15. Y. Terai, K. Noda, S. Hashimoto and Y. Fujiwara, Photoreflectance study of b-FeSi<sub>2</sub> epitaxial films grown by molecular beam epitaxy, Vol. 165, 012023/1-6, 2009
16. Y. Fujiwara, Y. Terai and A. Nishikawa, Development of new-type 1.5 μm light-emitting devices based on Er, O-codoped GaAs, *Journal of Physics: Conference Series*, Vol. 165, 012025/1-6, 2009
17. H. Kasai, A. Nishikawa, Y. Terai and Y. Fujiwara, Luminescence Properties of Eu-implanted GaN-based Semiconductors, *Journal of Physics: Conference Series*, Vol. 165, 012026/1-4, 2009
18. K. Yamaoka, Y. Terai, T. Yamaguchi, H. N. Ngo, T. Gregorkiewicz, and Y. Fujiwara, Metalorganic chemical vapor deposition of Er-doped ZnO thin films with 1.54 μm photoluminescence, *Journal of Physics: Conference Series*, Vol. 165, 012027/1-4, 2009